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~~21.~~ (New) A method of manufacturing a semiconductor device, comprising:
forming a soluble thin film which is soluble in a dissolving liquid on a film to be processed which is formed on a semiconductor substrate;
forming a mask layer on the soluble thin film;
forming an antireflection film on the mask layer;
forming a resist pattern on the antireflection film;
etching the antireflection film and the mask layer using the resist pattern as a mask to form a mask pattern;
etching the soluble thin film and the film to be processed using the mask pattern as at least a portion of a mask; and
dissolving the etched soluble thin film in the dissolving liquid, thereby lifting off the mask pattern from the film to be processed.

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~~22.~~ (New) A method according to claim ~~21~~⁶, wherein the antireflection film is an organic antireflection film.

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~~23.~~ (New) A method according to claim 1, further comprising the step of forming an antireflection film on the mask layer before the step of forming the resist pattern.--

REMARKS

In this Amendment, Applicants have amended the title and added new claims 21 – 23 to protect additional aspects of the present invention. In accordance with the requirements of 37 C.F.R. § 1.121(c)(1), Applicants provide a marked-up version of the title in an attached Appendix designated "Version of Title with Markings to Show Changes Made." Claims 1 – 23

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